# Design of a Low-Power Potentiostatic Second-Order CT Delta-Sigma ADC for Electrochemical Sensors

Joan Aymerich Gubern joan.aymerich@imb-cnm.csic.es

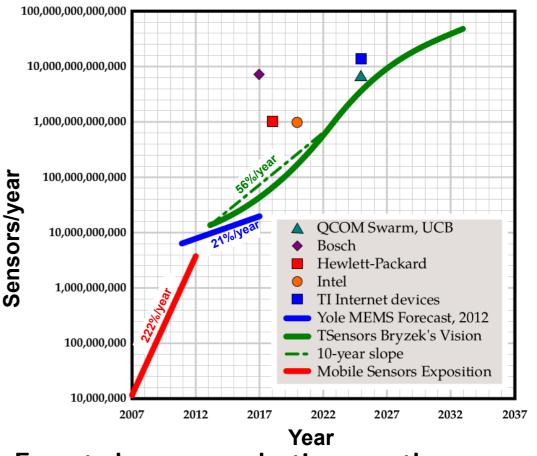
Integrated Circuits and Systems (ICAS) Instituto de Microelectrónica de Barcelona, IMB-CNM(CSIC)

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### **Trillion-Sensor Vision**

- Several organizations created visions for continued growth to trillion(s) sensors
  - **\$15 trillion by 2022**
- Electrochemical sensors are growing exponentially due to potential of miniaturization and mass production
  - Monolithic or hybrid integration onto CMOS platforms
  - Applications in biosensors, quality control, ...



Expected sensor production growth per year

www.tsensorssummit.org

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### **2** Potentiostatic $\Delta\Sigma$ Modulator architecture

3 Proposed architecture

4 Design methodology and trade-offs

### 5 Conclusions

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1 Amperometric Electrochemical Sensors

### 2 Potentiostatic $\Delta\Sigma$ Modulator architecture

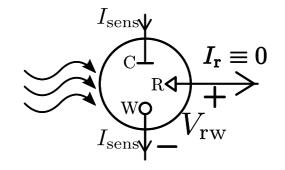
3 Proposed architecture

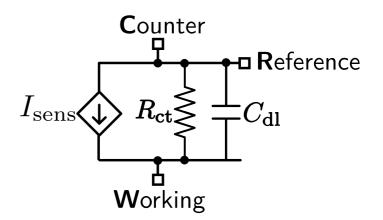
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### **Amperometric Electrochemical Sensors**

- ▲ Interaction with microorganisms
- ▲ **Selectivity** by functionalization
- Reduced speed and life time
- Potentiostatic and amperometric operations
- **Three electrodes:** 
  - Working
     Reference
     Counter
- Measurement independent of the R and C impedances.





- Electrochemical time constant:  $\tau_{\rm ch} = R_{\rm ct}C_{\rm dl} \approx 10^{-1}{\rm s}$ 
  - **Rct** = charge-transfer resistance
  - CdI = double-layer capacitance

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### **Classic circuit implementation**

#### Potentiostat

A<sub>1</sub> establishes the control loop to accomplish potentiostat operation

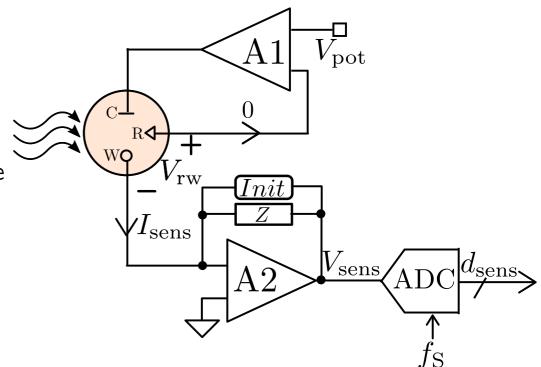
 $V_{
m rw}=V_{
m pot}$  &  $I_{
m r}\equiv 0$ 

#### Amperometry

A<sub>2</sub> converts sensor current to voltage for digitization and readout

Requires multiples OpAmps + ADC

Large area and power consumption







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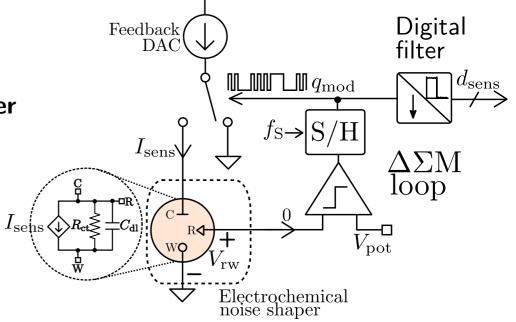
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## Potentiostatic $\Delta \Sigma M$

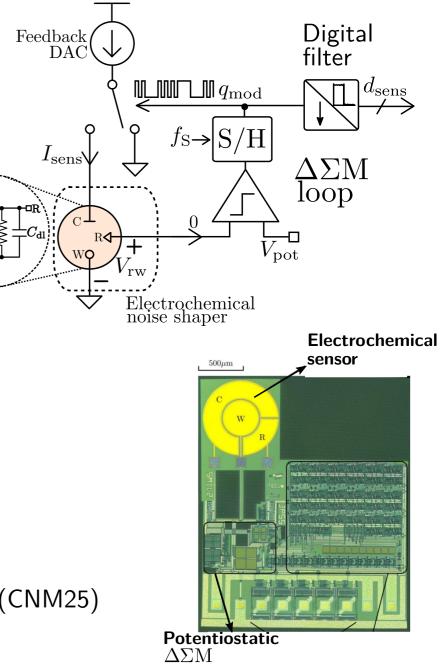
- ▶ Behaviour similar to low-pass first-order single-bit CT  $\Sigma\Delta M$  A/D modulator
- Error current converted into voltage and shaped in frequency by the electrochemical sensor itself
- ▲ High oversampling ratios (OSR>100) can be easly obtained with kHz-range clock frequencies f<sub>S</sub>
- Amperometric read-out through the  $\Delta\Sigma$ modulation of output bit stream  $q_{\rm mod}$ by chemical input  $I_{\rm sens}$



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Monolithic CMOS integration Inexpensive 2.5µm in-house CMOS technology (CNM25) developed by ICAS group at IMB-CNM(CSIC)



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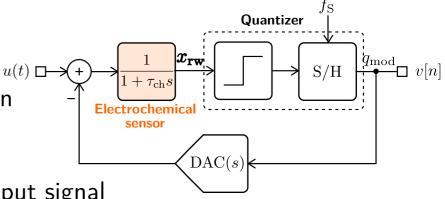
 $I_{\rm sehs}$ 

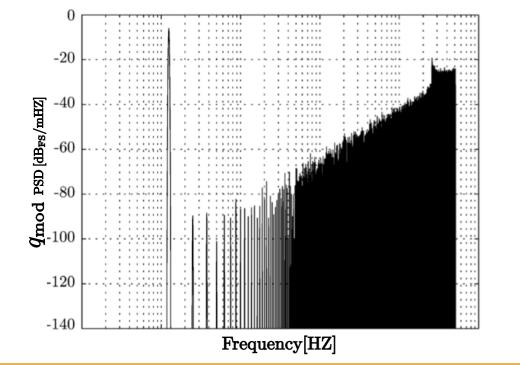
## Potentiostatic $\Delta \Sigma M$

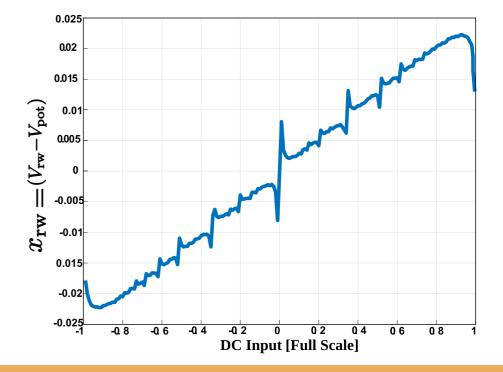
**v** Typical **tonal component** of  $1^{\text{st}}$  order  $\Delta \Sigma M$ 

- Quantization error and input signal correlation
- Potentiostat operation not well-defined

Potentiostatic error  $\mathcal{X}_{rw}$  influenced by the input signal







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### Proposed amperometric potentiostatic $\Sigma\Delta M$

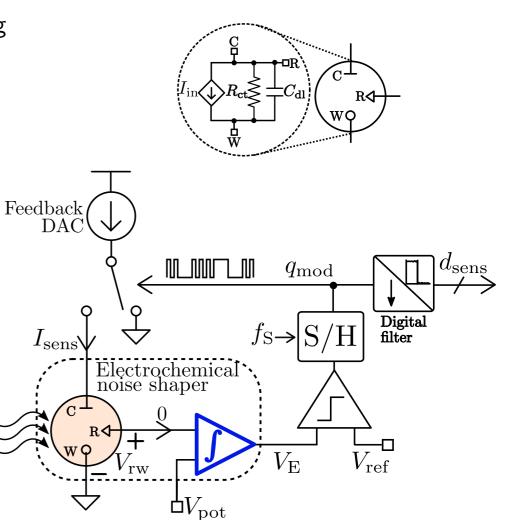
Incremental work: Addition of electronic integration

▲ **Higher resolution:** 2<sup>nd</sup> order noise shaping

- ▲ Idle tones attenuation
- ▲ Potentiostatic operation well-defined ■ Electronic integrator forces  $V_{rw} = V_{pot}$

▼ New design trade-offs!

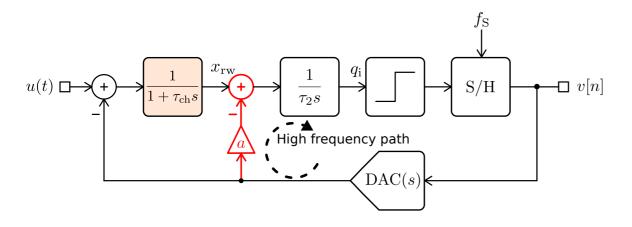
- **Stability compensation** is required
- A zero must be added in the loop filter to compensate the phase shift



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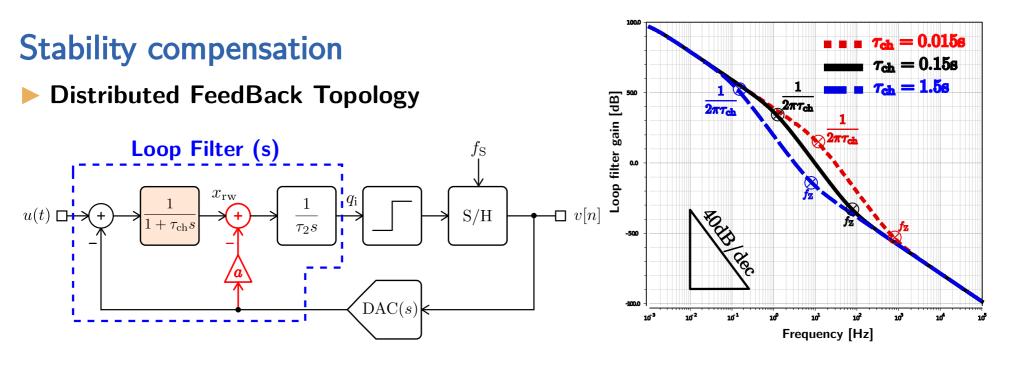
### Distributed FeedBack Topology



Loop Filter Zero frequency location

$$H_{\rm FB}(s) \approx \frac{1 + \frac{a}{1+a} \boldsymbol{\tau_{\rm ch}} s}{(1 + \boldsymbol{\tau_{\rm ch}} s) \boldsymbol{\tau_2} s} \quad ; \quad f_{\rm Z} = \frac{1+a}{2\pi a \boldsymbol{\tau_{\rm ch}}}$$



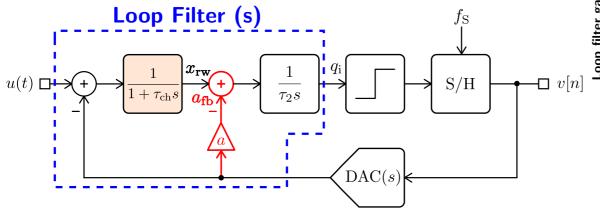


Loop Filter Zero frequency location

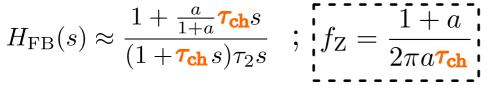
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▼  $f_Z$  depends on sensor time constant  $\tau_{ch}$ ■  $\downarrow \tau_{ch} \rightarrow \uparrow f_Z$  Leading to instability!!





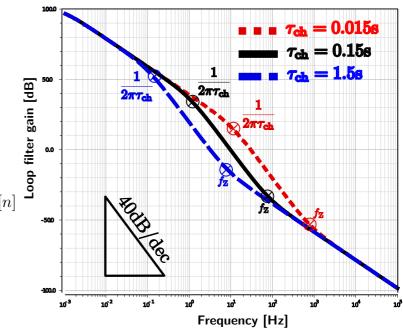
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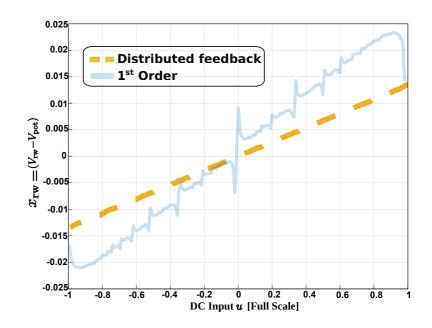


▼  $f_Z$  depends on sensor time constant  $\tau_{ch}$ ■  $\downarrow \tau_{ch} \rightarrow \uparrow f_Z$  Leading to unstability!!

Potentiostatic voltage strongly influenced by the sensor input signal

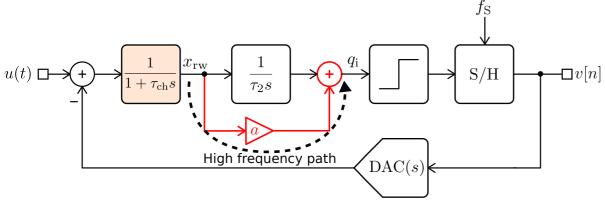
 $x_{\rm rw} = a_{\rm fb}$ 





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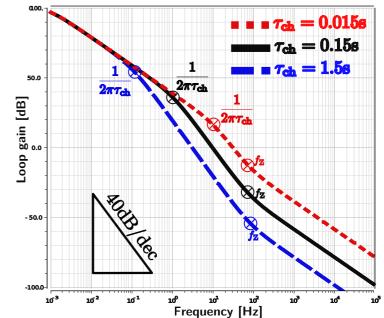
### Feed-Forward Topology



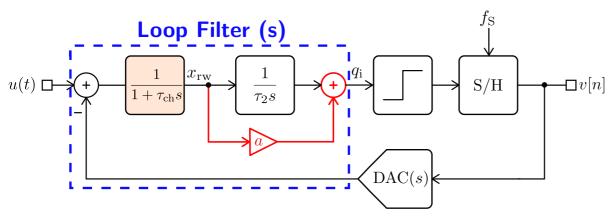
#### Loop Filter Zero frequency location

$$H_{\rm FF}(s) = \frac{1 + a\tau_2 s}{(1 + \tau_{\rm ch} s)\tau_2 s}; \quad f_{\rm Z} = \frac{1}{2\pi a\tau_2}$$

Variations in the sensor time constant do not compromise the stability of the system!



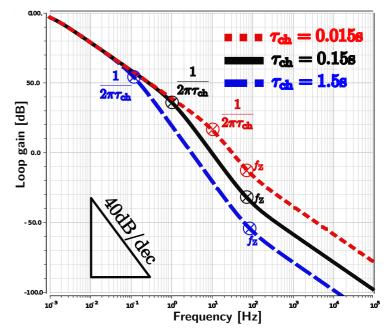
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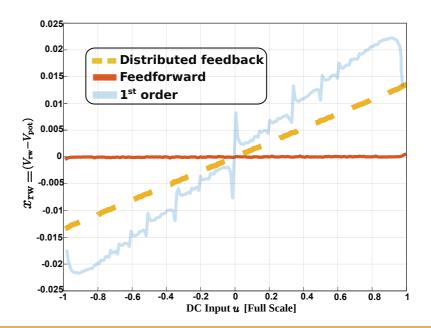


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- Variations in the sensor time constant do not compromise the stability of the system!
- **Electronic integrator forces** its input  $x_{rw}$  to have **DC zero component**.





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1 Amperometric Electrochemical Sensors

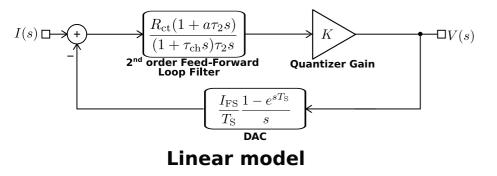
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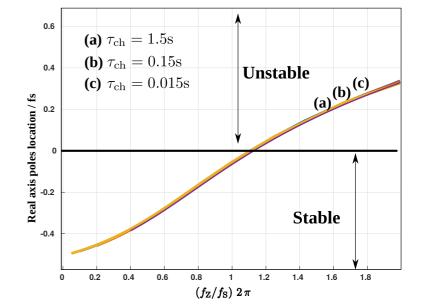
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#### Linear model

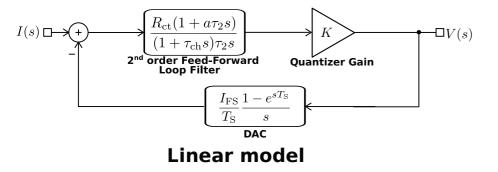


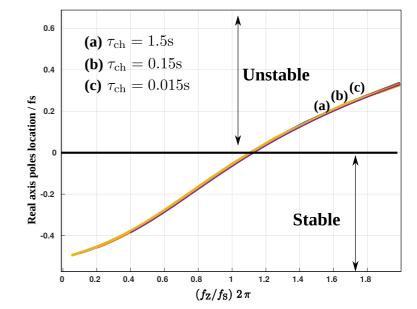


- Stability region as a function of f<sub>z</sub>/f<sub>s</sub>
  - **Root locus** analysis: Closed-loop poles moves as quantizer gain changes
  - Stability condition:  $f_{
    m Z} < f_{
    m S}/(2\pi)$

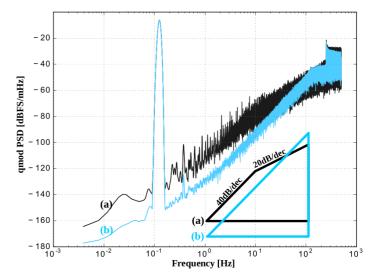
### **Small-Signal Stability Analysis**

#### Linear model





- Stability region as a function of f<sub>z</sub>/f<sub>s</sub>
  - **Root locus** analysis: Closed-loop poles moves as quantizer gain changes
  - Stability condition:  $f_{
    m Z} < f_{
    m S}/(2\pi)$
- Power Spectrum as function of zero location
  - More stable (More 1<sup>st</sup> order behaviour) Less aggressive noise shaping
    - Less safety stability margin Better noise shaping



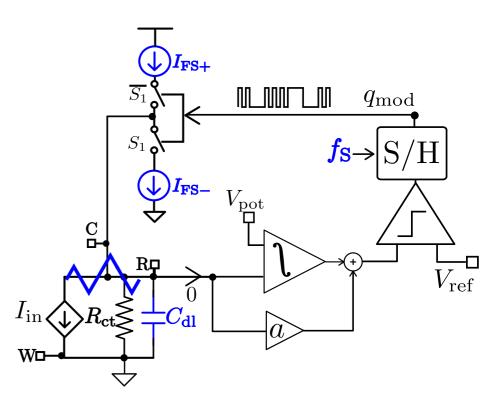
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## Potentiostat Voltage Ripple

- Voltage ripple may be required to be kept below certain minimum
- Feedback current DAC (I<sub>FS</sub>) charges/discharges Cdl
- T<sub>s</sub> is the only degree of freedom to minimize ripple
  - **(** $C_{dI}$  and **I**<sub>FS</sub> are fixed by the application)

$$\frac{\Delta V_{\rm rw}}{V_{\rm rw}} \propto \frac{I_{\rm FS} T_S / C_{\rm dl}}{I_{\rm FS} R_{\rm ct}} = \frac{T_{\rm S}}{\tau_1}$$



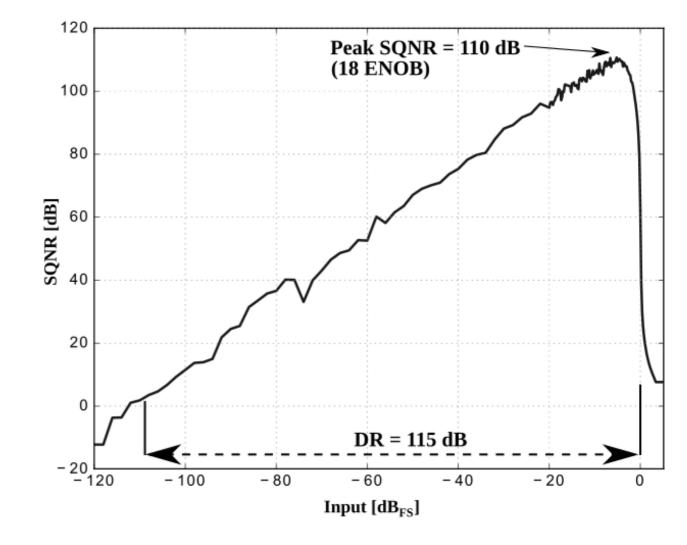
### SQNR vs input signal

Top-level simulation

 $f_S = 1k \text{Hz}$ 

- $\bullet \tau_{\rm ch} = 0.15 \mathrm{s}(OSR \approx 500)$
- $f_{\rm Z}/f_{\rm S} = 1/(4\pi)$

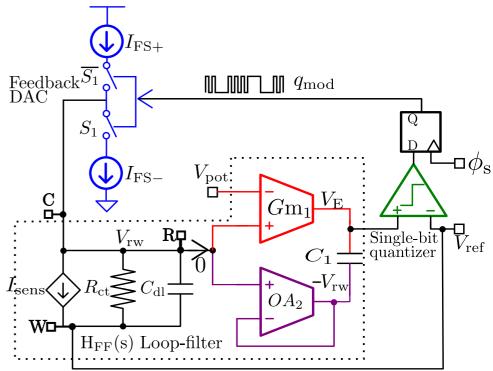
 $I_{\rm FS} = 2\mu A$ 





### Low-power circuit implementation

- Flexible and modular to be mapped into different CMOS technologies
- Electronic integrator: Gm<sub>1</sub>-C<sub>1</sub>
- Feed-Forward path
- Latch comparator for 1-bit quantization
- **D-type flip-flop** for S/H
- Feedback current DAC
  - Power consumption mainly determined by current DAC FS, allowing chemical reaction take place



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### **Simulation Results**

#### Performance simulation results

Power consumption mainly determined by current DAC FS  $P_{DAC} = 4.7 \mu W$ 

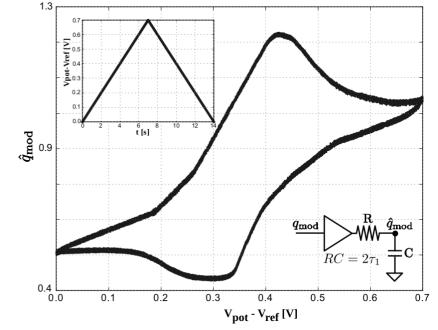
Rest of circuit blocks P = 370 nW

#### 0.18µm CMOS technology

Parameter	Symbol	Value	Unit
Supply voltage	$V_{\rm DD}$	1.8	V
Potential range	$V_{\rm pot} - V_{\rm ref}$	$\pm 0.7$	V
Input full scale	$I_{\rm FS}$	$\pm 2$	$\mu \mathrm{A}$
Oversampling ratio	OSR	500	—
Sampling frequency	$f_{ m S}$	1	m kHz
Loop-filer zero location	$f_{\rm Z}/f_{ m S}$	$1/\pi$	_
Potentiostatic ripple	$\Delta V_{ m rw}$	11.6	mVrms
Power at $2\mu A_{FS}$	$P_{\mathrm{D}}$	5.1	$\mu W$

#### Cyclic Voltammetry

- Method for studying electrochemical reactions
- Triangular waveform is applied to the Reference-electrode, while the sensor current is measured simultaneously.
- VerilogA model



Ferrocyanide Cyclic Voltammetry

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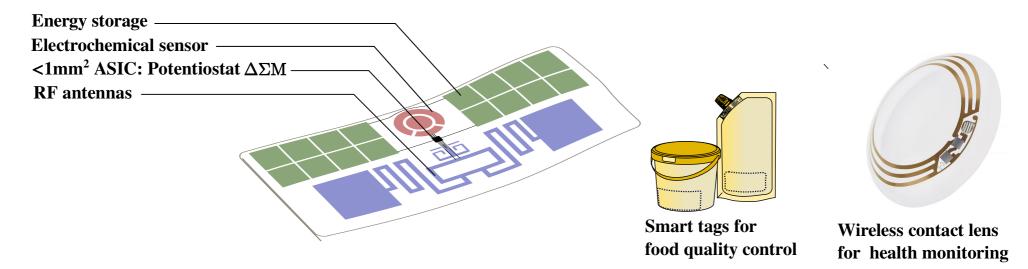
### Conclusions

- **Compact architecture** thanks to the electrode-electrolyte interface used as an integrator stage in the  $\Delta\Sigma$  structure
- Minimalist analog circuits fully integrable in purely digital CMOS technologies
- **High resolution** with kHz-range clock frequencies: SQNR = 110dB @ 1kHz
- $\triangleright$  Ultra low-power (370nW) operation compared to sensor consumption

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### **Future work**





### **Power Consumption Comparison**

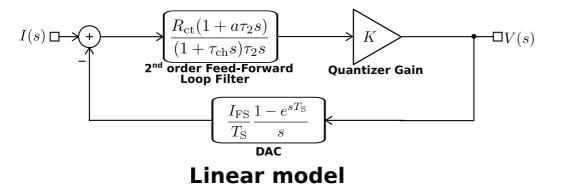
Technology	0.18 µm	0.5 µm	0.13 µm	0.18 µm	2.5 µm	0.18 µm	
ADC structure	Current to frequency	Delta-sigma	Single-Slope	Delta-sigma	Delta-sigma	Delta-sigma	
Sampling frequency	-	100 kHz	1.25 kHz	-	1 kHz	1 kHz	
FS current	150 nA	16 µA	600 nA	<b>1.65 μA</b>	2 μΑ	2 µA	
Power consumption	3 µW	241 µW	56 µW	920 μW	25 µW	5 µW	
@ supply voltage	@ 1.2 V	@ 1.2 V	@ 2 V	@ 1.8 V	@ 5 V	@ 1.8 V	

[This work]



### **Small-Signal Stability Analysis**

Linear model



#### Root Locus

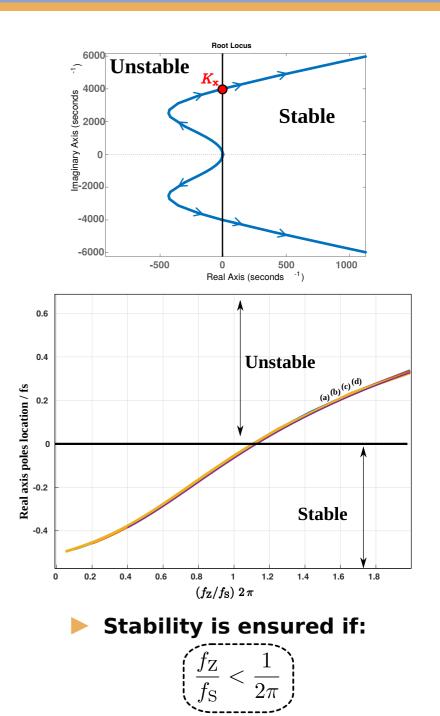
- Stability region as a function of K
- Worst-case scenario when K is maximum

#### From stable situation

Sweep input: 0 to FS to find maximum quantizer gain Kmax (worst-case)

#### Stability region as a function of f<sub>z</sub>/f<sub>s</sub>

Sweep  $f_S/f_Z$  and check if Kmax is within the stable region



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